U.S. Department of Commerce, Patent and Trademark	Atty. Docket No.	Application No.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	SNDK.256US0	10/052,924
	Applicant(s)	
(Use several sheets if necessary)	Mokhlesi et al.	
	Filing Date	Group
	January 18, 2002	2818

U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
HH	1	4,630,086	12/16/86	Sato et al.			
	2	5,172,338	12/15/92	Mehrotra et al.			
	3	5,172,338	7/8/97	Mehrotra et al.			
	4	5,418,752	5/23/95	Harari et al.			
	5	5,712,180	1/27/98	Guterman et al.			
	6	5,768,192	6/16/98	Eitan			
	7	5,892,706	4/6/99	Shimizu et al.			
	8	6,044,019	3/28/00	Cernea et al.			
	9	6,103,573	8/15/00	Harari et al.			
HH	10	6,222,762	4/24/01	Guterman et al.			

U.S. Published Patent Application Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate

Foreign Patent Documents

							Translation	
		Document	Date	Country	Class	Subclass	Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

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Examiner Huan Hoang	Date Considered 8/7/03

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.